

**isc N-Channel MOSFET Transistor**

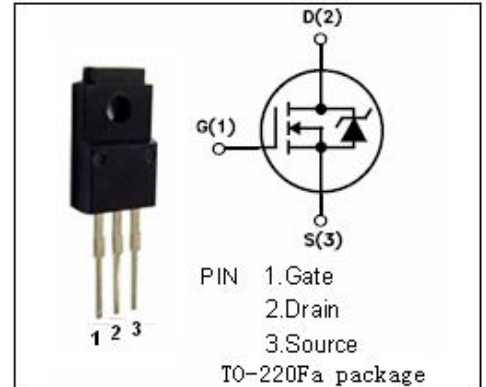
**2SK617**

**FEATURES**

- Drain Current  $-I_D=1A @ T_C=25^\circ C$
- Drain Source Voltage-  
:  $V_{DSS}= 800V(\text{Min})$

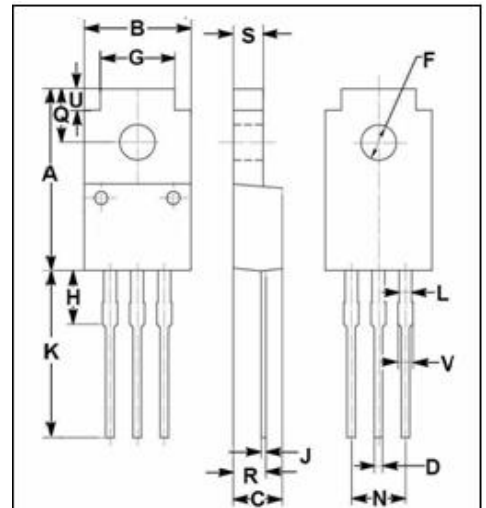
**DESCRIPTION**

- Designed for low voltage, high speed power switching applications such as switching regulators, converters, solenoid and relay drivers.



**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage	800	V
$V_{GS}$	Gate-Source Voltage-Continuous	$\pm 20$	V
$I_D$	Drain Current-Continuous	1	A
$P_D$	Total Dissipation @ $T_C=25^\circ C$	40	W
$T_J$	Max. Operating Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature	-55~150	$^\circ C$



DIM	mm	
	MIN	MAX
A	16.85	17.15
B	9.90	10.10
C	4.35	4.65
D	0.75	0.80
F	3.20	3.40
G	6.90	7.10
H	5.15	5.45
J	0.45	0.75
K	13.35	13.65
L	1.10	1.30
N	4.98	5.18
Q	4.85	5.15
R	2.95	3.25
S	2.70	2.90
U	1.75	2.05
V	1.30	1.50

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	1.25	$^\circ C/W$
$R_{th j-a}$	Thermal Resistance, Junction to Ambient	62.5	$^\circ C/W$

**isc N-Channel MOSFET Transistor****2SK617****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0; I_D=0.25\text{mA}$	800			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}; I_D=1\text{mA}$	2.1		4.0	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=15\text{V}; I_D=1\text{A}$			8	$\Omega$
$I_{GSS}$	Gate-Body Leakage Current	$V_{GS}=\pm 20\text{V}; V_{DS}=0$			$\pm 100$	nA
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=800\text{V}; V_{GS}=0$			1	mA